THIS SHEET HAS BEEN REPLACED

ABSTRACT:

The injection of minority carriers into a substrate caused by potential fluctuations ascribable to noise etc. is prevented.

In a semiconductor device which has sources and drains of insulated-gate field effect transistors or collectors, bases and emitters of bipolar transistors within a substrate and/or a plurality of isolation layers isolated in the substrate, voltages having values outside a varying range of applied voltages to respective electrodes of the source and drain or to the collector, base and emitter are applied to the substrate and the isolation layers.

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